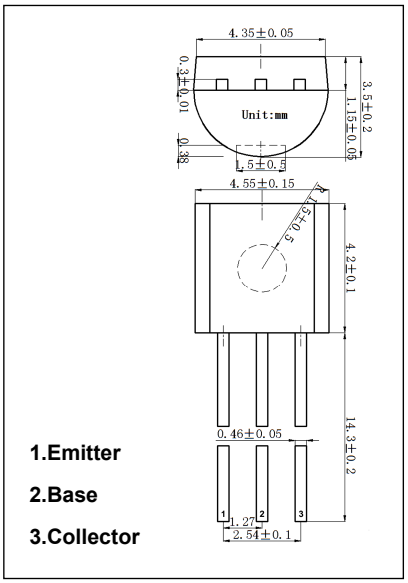
SHENZHEN LONG JING MICRO-ELECTRONICS CO., LTD.

TO-92 Plastic-Encapsulate Transistors

2N5401H-98 PNP Transistors



Features

- Switching and Amplification in High Voltage
- Applications such as Telephony
- Low Current
- High Voltage

Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector Emitter Voltage	-150	V
V_{CBO}	Collector Base Voltage	-160	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current	-600	mA
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-0.1mA,I_E=0	-160		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA,I_B=0	-150		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-0.01mA,I_C=0	-5		V
I_{CBO}	Collector cut-off current	V_{CB}=-120V,I_E=0		-50	nA
I_{EBO}	Emitter cut-off current	V_{EB}=-3V,I_C=0		-50	nA
$h_{FE(1)}$	Dc current gain	V_{CE}=-5V, I_C=-1mA	60		
$h_{FE(2)}$		V_{CE}=-5V, I_C=-10mA	60	300	
$h_{FE(3)}$		V_{CE}=-5V, I_C=-50mA	50		
$V_{CE\ (sat)}$	Collector-emitter saturation voltage	I_C=-50mA,I_B=-5mA		-0.5	V
$V_{BE\ (sat)}$	Base-emitter saturation voltage	I_C=-50mA,I_B=-5mA		-1	V
f_T	Transition frequency	V_{CE}=-5V,I_C=-10mA, f =30MHz	100	300	MHz

*Pulse test: Pulse Width <300μs, Duty Cycle<2.0%

Classification OF $h_{FE(1)}$

RANK		A	B	C
RANGE	100-160	100-150	150-200	200-300

Typical Characteristics